36V Rad Hard Dual Precision Operational Amplifier

ISL70227SEH

The ISL70227SEH is a high precision dual operational amplifier featuring very low noise, low offset voltage, low input bias current and low temperature drift. These features plus its radiation tolerance make the ISL70227SEH the ideal choice for applications requiring both high DC accuracy and AC performance. The combination of precision, low noise, and small footprint provides the user with outstanding value and flexibility relative to similar competitive parts.

Applications for these amplifiers include precision and analytical instrumentation, active filters, and power supply controls.

The ISL70227SEH is available in a 10 lead hermetic ceramic flatpack and operates over the extended temperature range of -55°C to +125°C.

Applications

- Power Supply Control
- Industrial Controls
- Active Filter Blocks
- Data Acquisition

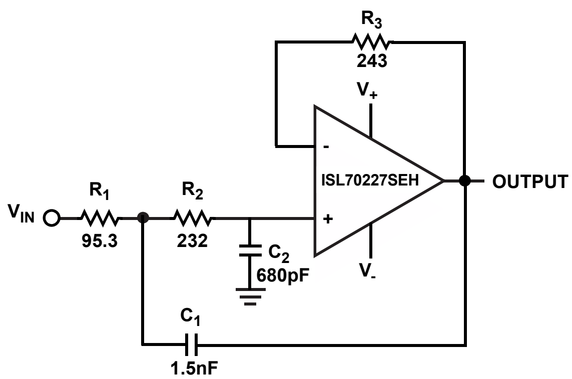
Features

- **Electrically Screened to DLA SMD# 5962-12223**
- **Wide Supply Range .4.5V to 42V Max.**
- **Very Low Voltage Noise . . . . .2.5nV/√Hz, Typ.**
- **Gain-bandwidth Product 10MHz**
- **Superb Offset Drift . . . . .1µV/°C, Max**
- Operating Temperature Range. . . . .-55°C to +125°C
- Low Input Voltage Offset. . . . . .10µV, Typ.
- Input Bias Current . . . . .1nA, Typ.
- Unity Gain Stable
- No Phase Reversal
- Radiation Tolerance
  - SEL/SEB LET_{TH} . . . . .86MeV•cm^2/mg
  - High Dose Rate. . . . . 100krad(Si)
  - Low Dose Rate . . . . 100krad(Si)*

* Product capability established by initial characterization. The EH version is acceptance tested on a wafer by wafer basis to 50krad(Si) at low dose rate.

Related Literature

- AN1669, "ISL70227SRH Evaluation Board User's Guide"
- AN1756, "Single Events Effects Testing of the ISL70227RH, Dual 36V Rad Hard Precision Operational Amplifiers"



Sallen-Key Low Pass Filter (1MHz)

FIGURE 1. TYPICAL APPLICATION

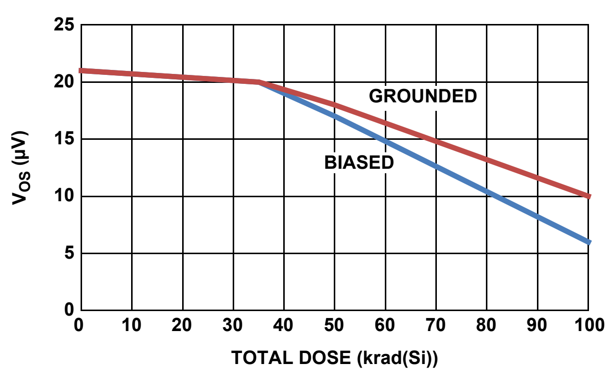


FIGURE 2. OFFSET VOLTAGE vs LOW DOSE RADIATION

Ordering Information

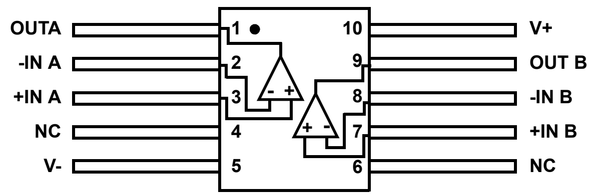
ORDERING NUMBER (Notes 1, 2)	PART MARKING	TEMP RANGE (°C)	PACKAGE (Pb-free)	PKG. DWG. #
5962R1222301VXA	ISL70227SEHVF	-55 to +125	10 Ld Flatpack	K10.A
ISL70227SEHF/PROTO	ISL70227 SEHF/PROTO	-55 to +125	10 Ld Flatpack	K10.A
5962R1222301V9A	ISL70227SEHVX	-55 to +125	Die	
ISL70227SEHX/SAMPLE	ISL70227SEHVX/SAMPLE	-55 to +125	Die	
ISL70227MHEVAL1Z	Evaluation Board			

NOTES:

1. These Intersil Pb-free Hermetic packaged products employ 100% Au plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations.
2. For Moisture Sensitivity Level (MSL), please see device information page for ISL70227SEH. For more information on MSL please see techbrief TB363.

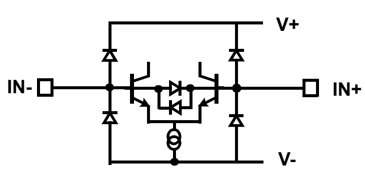
Pin Configuration

ISL70227SEH
(10 LD FLATPACK)
TOP VIEW

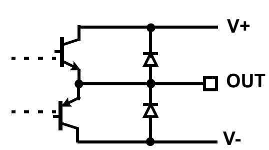


Pin Descriptions

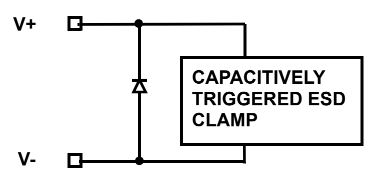
PIN NUMBER	PIN NAME	EQUIVALENT CIRCUIT	DESCRIPTION
3	+IN A	Circuit 1	Amplifier A non-inverting input
5	V-	Circuit 3	Negative power supply
7	+IN B	Circuit 1	Amplifier B non-inverting input
8	-IN B	Circuit 1	Amplifier B inverting input
9	OUT B	Circuit 2	Amplifier B output
10	V+	Circuit 3	Positive power supply
1	OUT A	Circuit 2	Amplifier A output
2	-IN A	Circuit 1	Amplifier A inverting input
4, 6	NC	-	Not Connected – This pin is not electrically connected internally.



CIRCUIT 1



CIRCUIT 2



CIRCUIT 3

Absolute Maximum Ratings

Maximum Supply Voltage 42V
Maximum Supply Voltage (LET = 86.4 MeV • cm^2/mg) 36V
Maximum Differential Input Current 20mA
Maximum Differential Input Voltage 0.5V
Min/Max Input Voltage . . . . V_- - 0.5V to V_+ + 0.5V
Max/Min Input Current for
Input Voltage >V+ or <V- . . . . ±20mA
Output Short-Circuit Duration
(1 output at a Time) . . . . Indefinite
ESD Tolerance
Human Body Model (Tested per MIL-PRF-883 3015.7) 2kV
Machine Model (Tested per JESD22-A115-A) 300V
Charged Device Model (Tested per CDM-22CI0ID) 750V
Di-electrically Isolated PR40 Process . . . . Latch-up free

Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)	θ_{JC} (°C/W)
10 Ld Ceramic Flatpack (Notes 3, 4)	130	20

Storage Temperature Range . . . . -65°C to +150°C
Pb-Free Reflow Profile . . . . see link below
http://www.intersil.com/pbfree/Pb-FreeReflow.asp

Recommended Operating Conditions

Ambient Operating Temperature Range . . . . -55°C to +125°C
Maximum Operating Junction Temperature . . . . +150°C
Supply Voltage . . . . 4.5V (±2.25V) to 30V (±15V)

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTES:

3. θ_{JA} is measured with the component mounted on a low effective thermal conductivity test board in free air. See Tech Brief TB379 for details.
4. For θ_{JC}, the "case temp" location is the center of the ceramic on the package underside.

Electrical Specifications

V_S ±15V, V_{CM} = 0, V_O = 0V, R_L = Open, T_A = +25°C, unless otherwise noted. **Boldface limits apply over the operating temperature range, -55°C to +125°C.**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 5)	TYP	MAX (Note 5)	UNIT
V_{OS}	Offset Voltage		-75	-10	75	µV
			-100		**100**	µV
TCV_{OS}	Offset Voltage Drift		**-1**	.1	**1**	µV/°C
I_{OS}	Input Offset Current		-10	1	10	nA
			-12		**12**	nA
I_B	Input Bias Current		-10	1	10	nA
			-12		**12**	nA
V_{CM}	Input Voltage Range	Guaranteed by CMRR	-13		13	V
			-12		**12**	V
CMRR	Common-Mode Rejection Ratio	V_{CM} = -13V to +13V	115	120		dB
		V_{CM} = -12V to +12V	**115**			dB
PSRR	Power Supply Rejection Ratio	V_S = ±2.25V to ±5V	110	117		dB
		V_S = ±3V to ±15V	**110**			dB
A_{VOL}	Open-Loop Gain	V_O = -13V to +13V R_L = 10kΩ to ground	1000	1500		V/mV
V_{OH}	Output Voltage High	R_L = 10kΩ to ground	13.5	13.65		V
			13.2			V
		R_L = 2kΩ to ground	13.4	13.5		V
			13.1			V
V_{OL}	Output Voltage Low	R_L = 10kΩ to ground		-13.65	-13.5	V
					-13.2	V
		R_L = 2kΩ to ground		-13.5	-13.4	V
					-13.1	V

Electrical Specifications V_S ±15V, V_{CM} = 0, V_O = 0V, R_L = Open, T_A = +25°C, unless otherwise noted. **Boldface limits apply over the operating temperature range, -55°C to +125°C. (Continued)**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 5)	TYP	MAX (Note 5)	UNIT
I_S	Supply Current/Amplifier			2.2	2.8	mA
					3.7	mA
I_{SC}	Short-Circuit	R_L = 0Ω to ground		±45		mA
V_{SUPPLY}	Supply Voltage Range	Guaranteed by PSRR	±2.25		±15	V
AC SPECIFICATIONS						
GBW	Gain Bandwidth Product			10		MHz
e_{np-p}	Voltage Noise	0.1Hz to 10Hz		85		nV_{P-P}
e_n	Voltage Noise Density	f = 10Hz		3		nV/√Hz
e_n	Voltage Noise Density	f = 100Hz		2.8		nV/√Hz
e_n	Voltage Noise Density	f = 1kHz		2.5		nV/√Hz
e_n	Voltage Noise Density	f = 10kHz		2.5		nV/√Hz
in	Current Noise Density	f = 10kHz		0.4		pA/√Hz
THD + N	Total Harmonic Distortion + Noise	1kHz, G = 1, V_O = 3.5V_{RMS}, R_L = 2kΩ		0.00022		%
TRANSIENT RESPONSE						
SR	Slew Rate	A_V = 10, R_L = 2kΩ, V_O = 4V_{P-P}	±2.5	±3.6		V/µs
			±2.0			V/µs
t_r, t_f, Small Signal	Rise Time 10% to 90% of V_{OUT}	A_V = -1, V_{OUT} = 100mV_{P-P}, R_f = R_g = 2kΩ, R_L = 2kΩ to V_{CM}		36	100	ns
					100	ns
	Fall Time 90% to 10% of V_{OUT}	A_V = -1, V_{OUT} = 100mV_{P-P}, R_f = R_g = 2kΩ, R_L = 2kΩ to V_{CM}		38	100	ns
					100	ns
t_s	Settling Time to 0.1% 10V Step; 10% to V_{OUT}	A_V = -1, V_{OUT} = 10V_{P-P}, R_g = R_f = 10k, R_L = 2kΩ to V_{CM}		3.4		µs
	Settling Time to 0.01% 10V Step; 10% to V_{OUT}	A_V = -1, V_{OUT} = 10V_{P-P}, R_L = 2kΩ to V_{CM}		3.8		µs
t_{OL}	Output Overload Recovery Time	A_V = 100, V_{IN} = 0.2V, R_L = 2kΩ to V_{CM}		1.7		µs
OS+	Positive Overshoot	A_V = 1, V_{OUT} = 10V_{P-P}, R_f = 0Ω R_L = 2kΩ to V_{CM}		20		%
					35	%
OS-	Negative Overshoot	A_V = 1, V_{OUT} = 10V_{P-P}, R_f = 0Ω R_L = 2kΩ to V_{CM}		20		%
					35	%

Electrical Specifications

V_S ±15V, V_{CM} = 0, V_O = 0V, R_L = Open, T_A= +25°C, unless otherwise noted. **Boldface limits apply over a total ionizing dose of 100krad(Si) with exposure at a high dose rate of 50 - 300krad(Si)/s; and over a total ionizing dose of 50krad(Si) with exposure at a low dose rate of <10mrad(Si)/s.**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 5)	TYP	MAX (Note 5)	UNIT
V_{OS}	Offset Voltage		-75	-10	75	µV
			-100		**100**	µV
TCV_{OS}	Offset Voltage Drift		**-1**	.1	**1**	µV/°C
I_{OS}	Input Offset Current		-10	1	10	nA
			-25		**25**	nA
I_B	Input Bias Current		-10	1	10	nA
			-25		**25**	nA
V_{CM}	Input Voltage Range	Guaranteed by CMRR	-13		13	V
			-12		**12**	V
CMRR	Common-Mode Rejection Ratio	V_{CM} = -13V to +13V	115	120		dB
		V_{CM} = -12V to +12V	**115**			dB
PSRR	Power Supply Rejection Ratio	V_S = ±2.25V to ±5V	110	117		dB
		V_S = ±3V to ±15V	**110**			dB
A_{VOL}	Open-Loop Gain	V_O = -13V to +13V R_L = 10kΩ to ground	1000	1500		V/mV
V_{OH}	Output Voltage High	R_L = 10kΩ to ground	13.5	13.65		V
			13.2			V
		R_L = 2kΩ to ground	13.4	13.5		V
			13.1			V
V_{OL}	Output Voltage Low	R_L = 10kΩ to ground		-13.65	-13.5	V
					-13.2	V
		R_L = 2kΩ to ground		-13.5	-13.4	V
					-13.1	V
I_S	Supply Current/Amplifier			2.2	2.8	mA
					3.7	mA
I_{SC}	Short-Circuit	R_L = 0Ω to ground		±45		mA
V_{SUPPLY}	Supply Voltage Range	Guaranteed by PSRR	±2.25		±15	V
AC SPECIFICATIONS						
GBW	Gain Bandwidth Product			10		MHz
e_{np-p}	Voltage Noise	0.1Hz to 10Hz		85		nV_{P-P}
e_n	Voltage Noise Density	f = 10Hz		3		nV/√Hz
e_n	Voltage Noise Density	f = 100Hz		2.8		nV/√Hz
e_n	Voltage Noise Density	f = 1kHz		2.5		nV/√Hz
e_n	Voltage Noise Density	f = 10kHz		2.5		nV/√Hz
in	Current Noise Density	f = 10kHz		0.4		pA/√Hz
THD + N	Total Harmonic Distortion + Noise	1kHz, G = 1, V_O = 3.5V_{RMS}, R_L = 2kΩ		0.00022		%

Electrical Specifications

V_S ±15V, V_{CM} = 0, V_O = 0V, R_L = Open, T_A= +25°C, unless otherwise noted. **Boldface limits apply over a total ionizing dose of 100krad(Si) with exposure at a high dose rate of 50 - 300krad(Si)/s; and over a total ionizing dose of 50krad(Si) with exposure at a low dose rate of <10mrad(Si)/s. (Continued)**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 5)	TYP	MAX (Note 5)	UNIT
TRANSIENT RESPONSE						
SR	Slew Rate	A_V = 10, R_L = 2kΩ, V_O = $4V_{P-P}$	±2.5	±3.6		V/µs
			±2.0			V/µs
t_r, t_f, Small Signal	Rise Time 10% to 90% of V_{OUT}	A_V = -1, V_{OUT} = $100mV_{P-P}$, R_f = R_g = 2kΩ, R_L = 2kΩ to V_{CM}		36	100	ns
					100	ns
	Fall Time 90% to 10% of V_{OUT}	A_V = -1, V_{OUT} = $100mV_{P-P}$, R_f = R_g = 2kΩ, R_L = 2kΩ to V_{CM}			100	ns
					100	ns
t_s	Settling Time to 0.1% 10V Step; 10% to V_{OUT}	A_V = -1, V_{OUT} = $10V_{P-P}$, R_g = R_f = 10k, R_L = 2kΩ to V_{CM}		3.4		µs
	Settling Time to 0.01% 10V Step; 10% to V_{OUT}	A_V = -1, V_{OUT} = $10V_{P-P}$, R_L = 2kΩ to V_{CM}		3.8		µs
t_{OL}	Output Overload Recovery Time	A_V = 100, V_{IN} = 0.2V, R_L = 2kΩ to V_{CM}		1.7		µs
OS+	Positive Overshoot	A_V = 1, V_{OUT} = $10V_{P-P}$, R_f = 0Ω R_L = 2kΩ to V_{CM}		20		%
					35	%
OS-	Negative Overshoot	A_V = 1, V_{OUT} = $10V_{P-P}$, R_f = 0Ω R_L = 2kΩ to V_{CM}		20		%
					35	%

Electrical Specifications

V_S ±5V, V_{CM} = 0, V_O = 0V, T_A = +25°C, unless otherwise noted. **Boldface limits apply over the operating temperature range, -55°C to +125°C.**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 5)	TYP	MAX (Note 5)	UNIT
V_{OS}	Offset Voltage			-10		µV
TCV_{OS}	Offset Voltage Drift			.1		µV/°C
I_{OS}	Input Offset Current			1		nA
I_B	Input Bias Current			1		nA
CMRR	Common-Mode Rejection Ratio	V_{CM} = -3V to +3V		120		dB
PSRR	Power Supply Rejection Ratio	V_S = ±2.25V to ±5V		125		dB
A_{VOL}	Open-Loop Gain	V_O = -3V to +3V R_L = 10kΩ to ground		1500		V/mV
V_{OH}	Output Voltage High	R_L = 10kΩ to ground		3.65		V
		R_L = 2kΩ to ground		3.5		V
V_{OL}	Output Voltage Low	R_L = 10kΩ to ground		-3.65		V
		R_L = 2kΩ to ground		-3.5		V
I_S	Supply Current/Amplifier			2.2		mA
I_{SC}	Short-Circuit			±45		mA

Electrical Specifications

V_S ±5V, V_{CM} = 0, V_O = 0V, T_A = +25°C, unless otherwise noted. **Boldface limits apply over the operating temperature range, -55°C to +125°C. (Continued)**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 5)	TYP	MAX (Note 5)	UNIT
AC SPECIFICATIONS						
GBW	Gain Bandwidth Product			10		MHz
THD + N	Total Harmonic Distortion + Noise	1kHz, G = 1, Vo = 2.5V_{RMS}, R_L = 2kΩ		0.0034		%
TRANSIENT RESPONSE						
SR	Slew Rate	A_V = 10, R_L = 2kΩ		±3.6		V/µs
t_r, t_f, Small Signal	Rise Time 10% to 90% of V_{OUT}	A_V = -1, V_{OUT} = 100mV_{P-P}, R_f = R_g = 2kΩ, R_L = 2kΩ to V_{CM}		36		ns
	Fall Time 90% to 10% of V_{OUT}	A_V = -1, V_{OUT} = 100mV_{P-P}, R_f = R_g = 2kΩ, R_L = 2kΩ to V_{CM}		38		ns
t_s	Settling Time to 0.1%	A_V = -1, V_{OUT} = 4V_{P-P}, R_f = R_g = 2kΩ, R_L = 2kΩ to V_{CM}		1.6		µs
	Settling Time to 0.01%	A_V = -1, V_{OUT} = 4V_{P-P}, R_f = R_g = 2kΩ, R_L = 2kΩ to V_{CM}		4.2		µs

NOTE:

5. Compliance to datasheet limits is assured by one or more methods: production test, characterization and/or design.

High Dose Rate Post Radiation Characteristics

V_S ±15V, V_{CM} = 0V, V_O = 0V, R_L = Open, T_A = +25°C, unless otherwise noted. **This data is typical test data post radiation exposure at a rate of 50 to 300rad(Si)/s. This data is intended to show typical parameter shifts due to high dose rate radiation. These are not limits nor are they guaranteed.**

PARAMETER	DESCRIPTION	CONDITIONS	50k RAD	75k RAD	100k RAD	UNIT
V_{OS}	Offset Voltage		34	30	30	µV
I_{OS}	Input Offset Current		-1	-1	-2	nA
I_B	Input Bias Current		-1	-2	-3	nA
CMRR	Common-Mode Rejection Ration	V_{CM} = -13V to +13V	155	155	155	dB
PSRR	Power Supply Rejection Ratio	V_S = ±2.25V to ±15V	116	116	116	dB
A_{VOL}	Open-Loop Gain	V_O = -13V to +13V, R_L = 10kΩ to ground	3500	3500	3500	V/mV
I_S	Supply Current/Amplifier		2.2	2.2	2.2	mA

Low Dose Rate Post Radiation Characteristics

V_S ±15V, V_{CM} = 0V, V_O = 0V, R_L = Open, T_A = +25°C, unless otherwise noted. **This data is typical test data post radiation exposure at a rate of 10mrad(Si)/s. This data is intended to show typical parameter shifts due to low dose rate radiation. These are not limits nor are they guaranteed .**

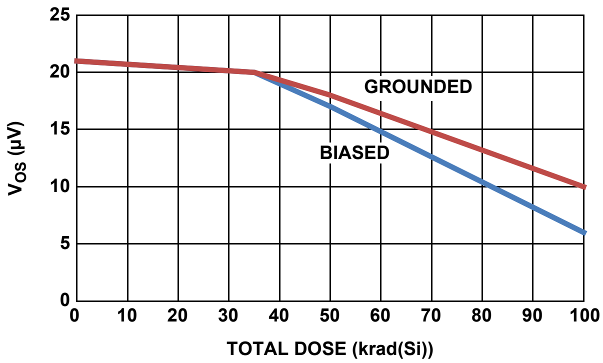


FIGURE 3. OFFSET VOLTAGE vs RADIATION

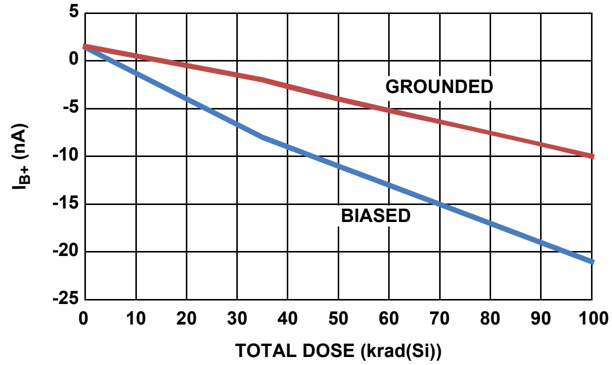


FIGURE 4. POSITIVE INPUT BIAS CURRENT vs RADIATION

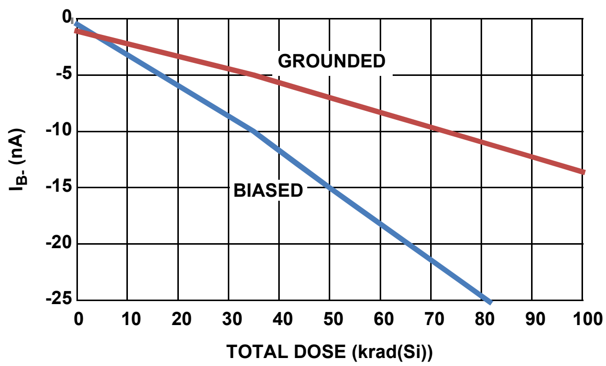


FIGURE 5. NEGATIVE INPUT BIAS CURRENT vs RADIATION

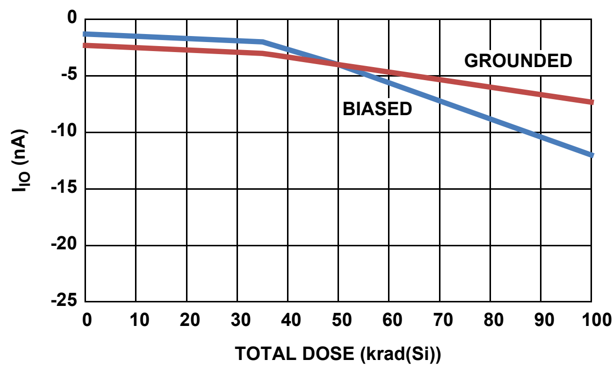


FIGURE 6. OFFSET CURRENT vs RADIATION

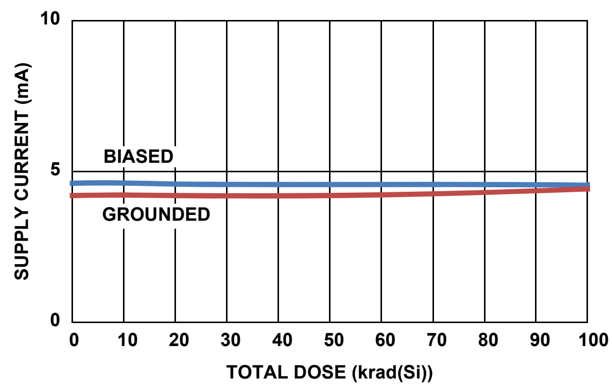


FIGURE 7. TOTAL SUPPLY CURRENT vs RADIATION

Typical Performance Curves V_S = ±15V, V_{CM} = 0V, R_L = Open, T_A = +25°C, unless otherwise specified.

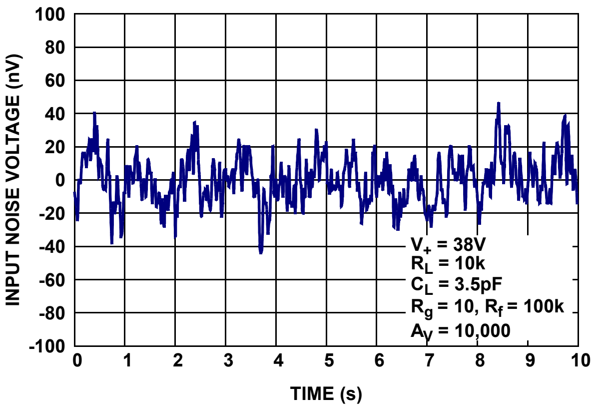


FIGURE 8. INPUT NOISE VOLTAGE 0.1Hz TO 10Hz

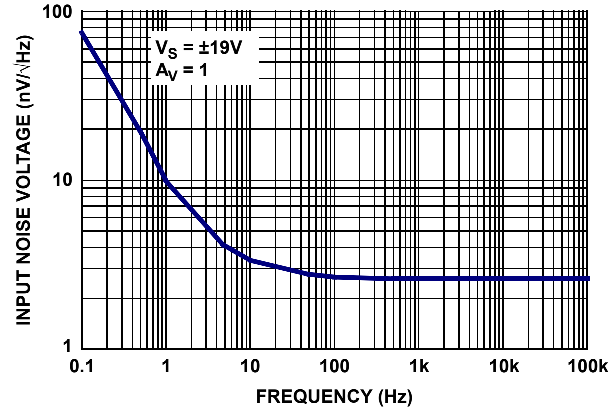


FIGURE 9. INPUT NOISE VOLTAGE SPECTRAL DENSITY

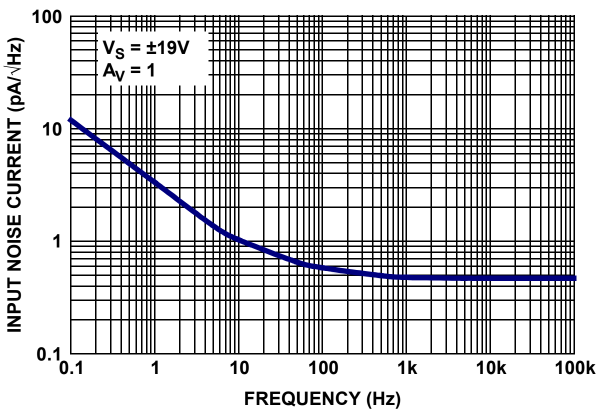


FIGURE 10. INPUT NOISE CURRENT SPECTRAL DENSITY

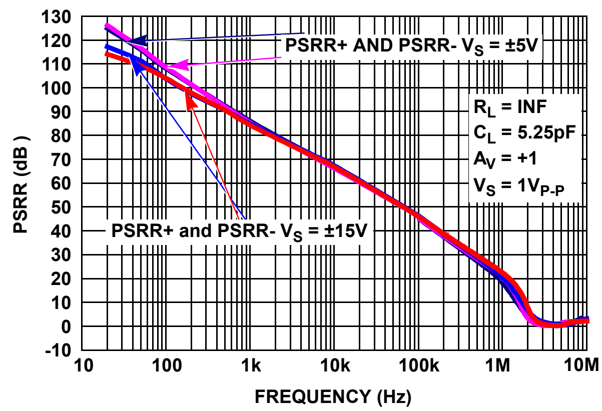


FIGURE 11. PSRR vs FREQUENCY, V_S = ±5V, ±15V

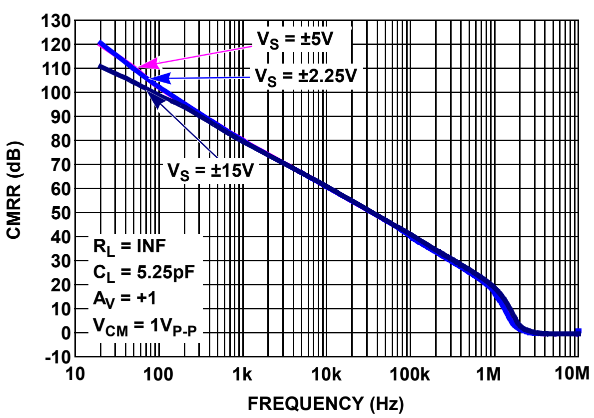


FIGURE 12. CMRR vs FREQUENCY, V_S = ±2.25, ±5V, ±15V

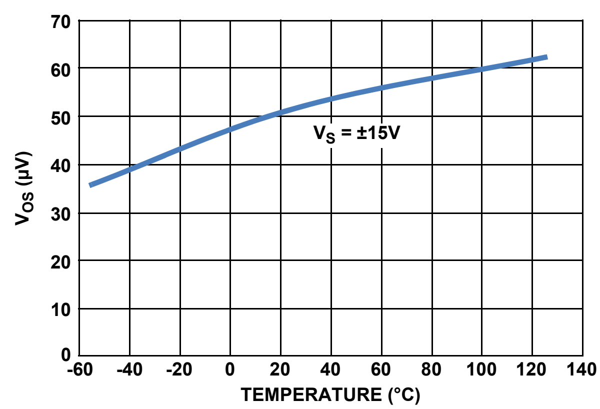


FIGURE 13. V_{OS} vs TEMPERATURE

Typical Performance Curves
V_S = ±15V, V_{CM} = 0V, R_L = Open, T_A = +25°C, unless otherwise specified. **(Continued)**

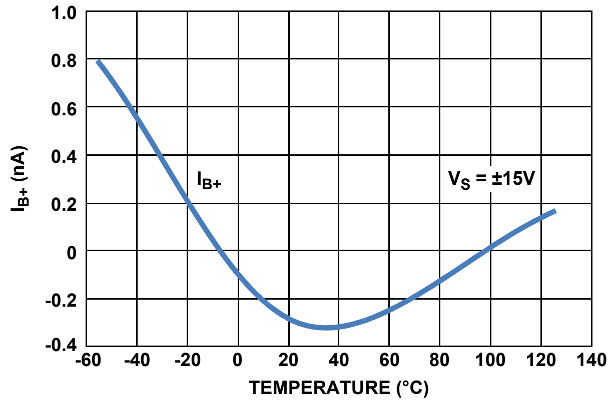


FIGURE 14. I_{B+} vs TEMPERATURE

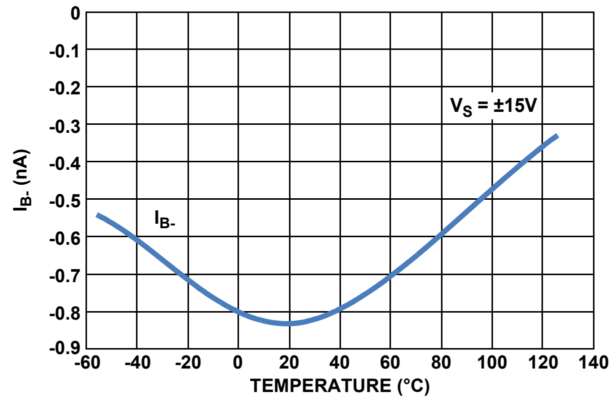


FIGURE 15. I_{B-} vs TEMPERATURE

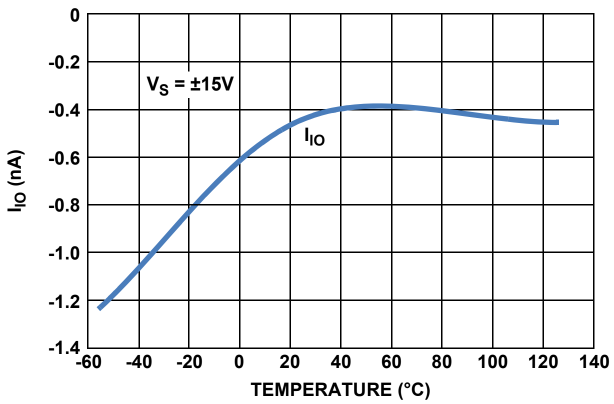


FIGURE 16. I_{OS} vs TEMPERATURE

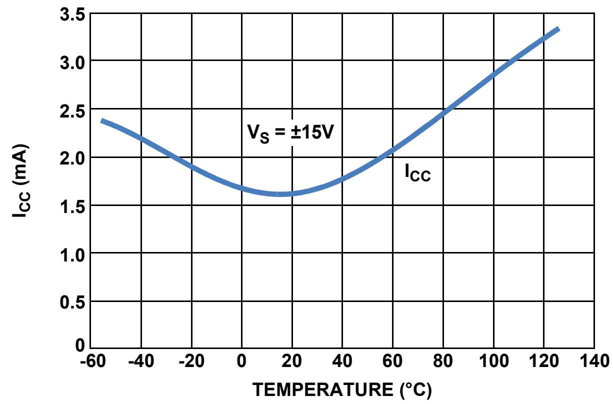


FIGURE 17. SUPPLY CURRENT vs TEMPERATURE

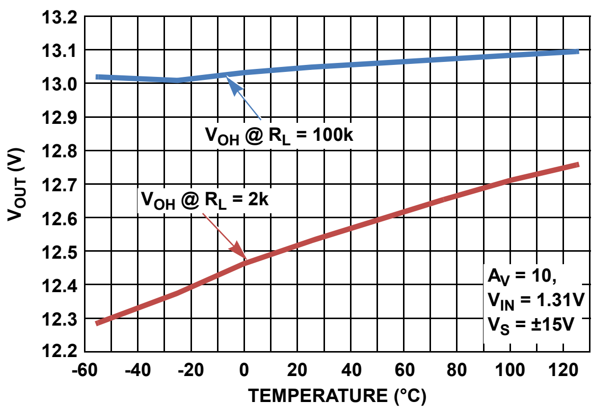


FIGURE 18. V_{OH} vs TEMPERATURE, V_S = ±15V

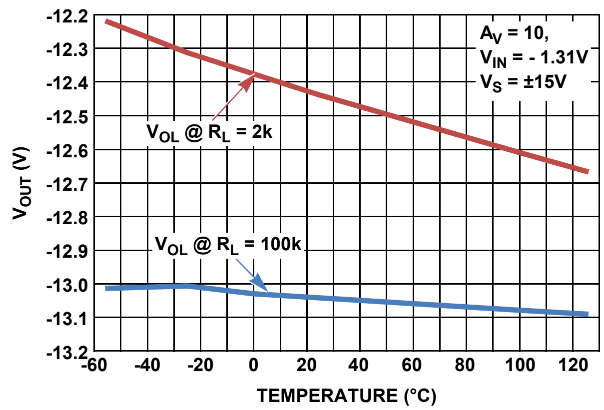


FIGURE 19. V_{OL} vs TEMPERATURE, V_S = ±15V

Typical Performance Curves

V_S = ±15V, V_{CM} = 0V, R_L = Open, T_A = +25°C, unless otherwise specified. **(Continued)**

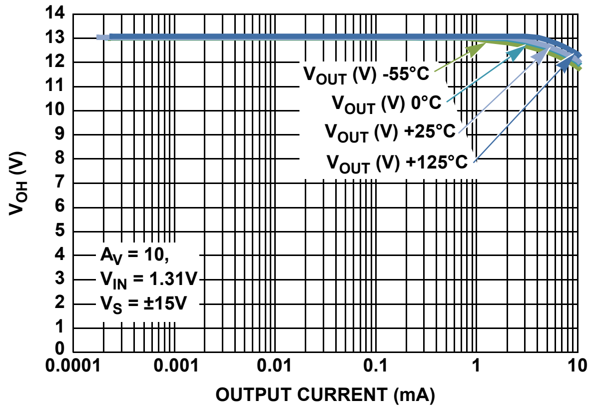


FIGURE 20. V_{OH} vs OUTPUT CURRENT

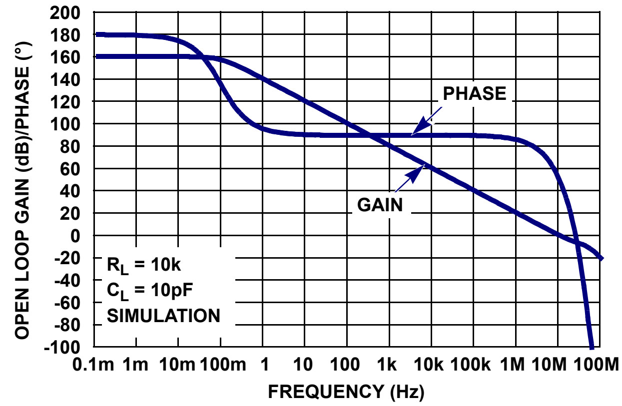


FIGURE 21. OPEN-LOOP GAIN, PHASE vs FREQUENCY, R_L = 10kΩ, C_L = 10pF

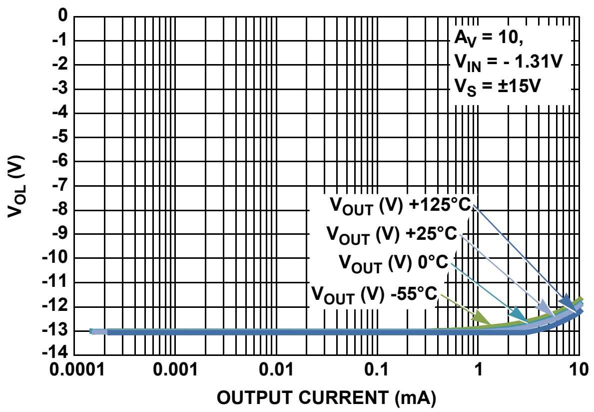


FIGURE 22. V_{OL} vs OUTPUT CURRENT

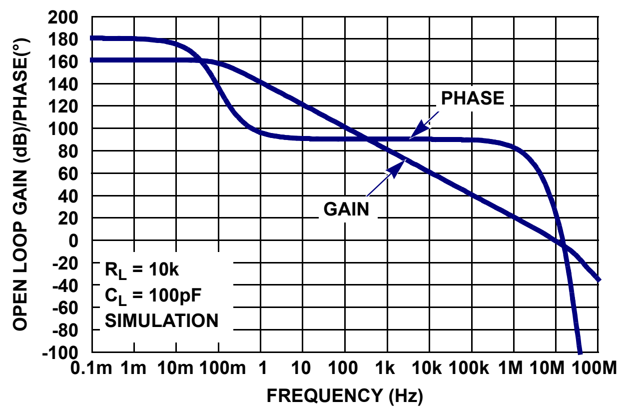


FIGURE 23. OPEN-LOOP GAIN, PHASE vs FREQUENCY, R_L = 10kΩ, C_L = 100pF

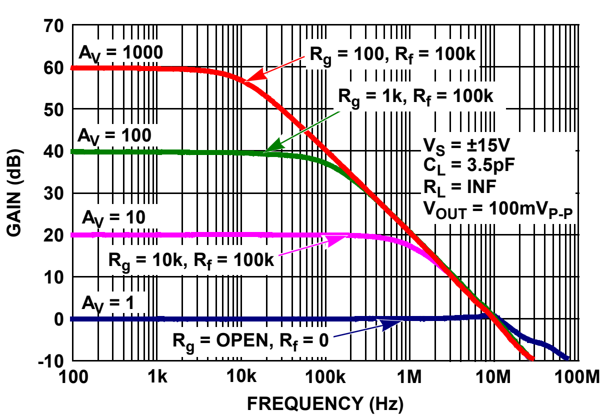


FIGURE 24. FREQUENCY RESPONSE vs CLOSED LOOP GAIN

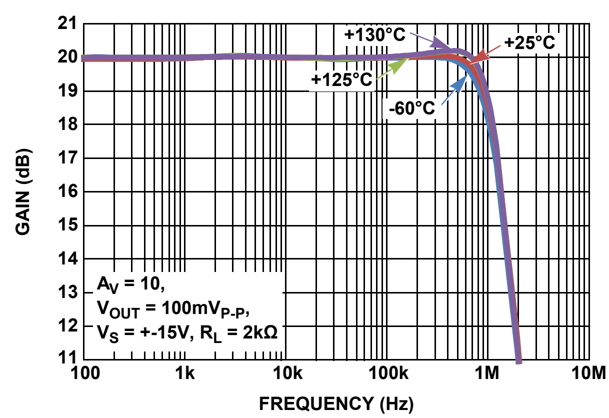


FIGURE 25. GAIN vs FREQUENCY vs TEMPERATURE

Typical Performance Curves

V_S = ±15V, V_{CM} = 0V, R_L = Open, T_A = +25°C, unless otherwise specified. **(Continued)**

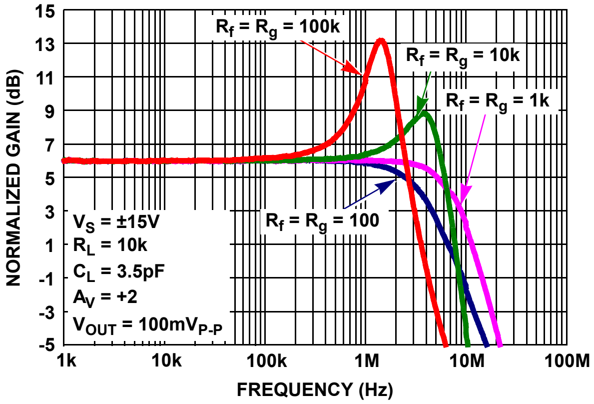


FIGURE 26. FREQUENCY RESPONSE vs FEEDBACK RESISTANCE R_f/R_g

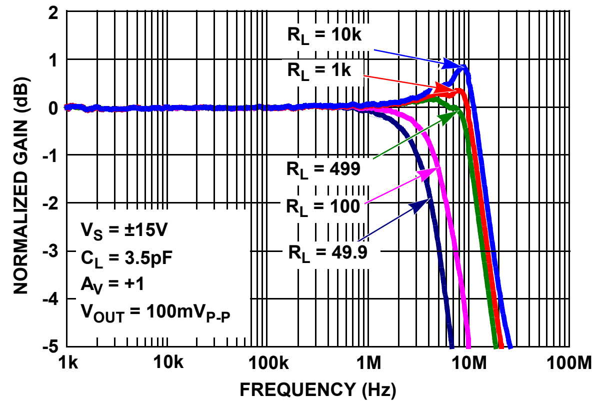


FIGURE 27. GAIN vs FREQUENCY vs R_L

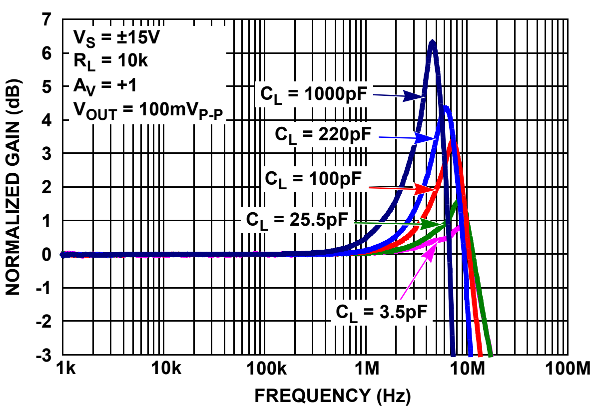


FIGURE 28. GAIN vs FREQUENCY vs C_L

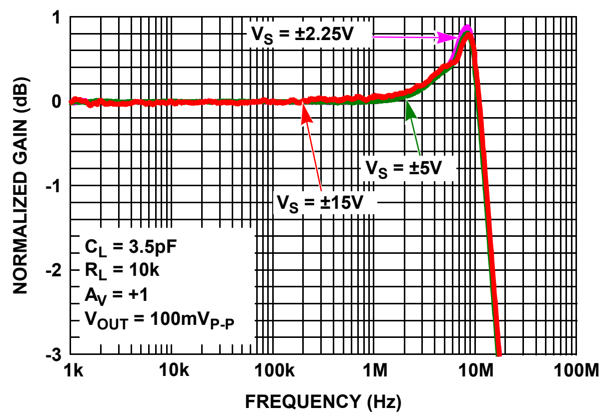


FIGURE 29. GAIN vs FREQUENCY vs SUPPLY VOLTAGE

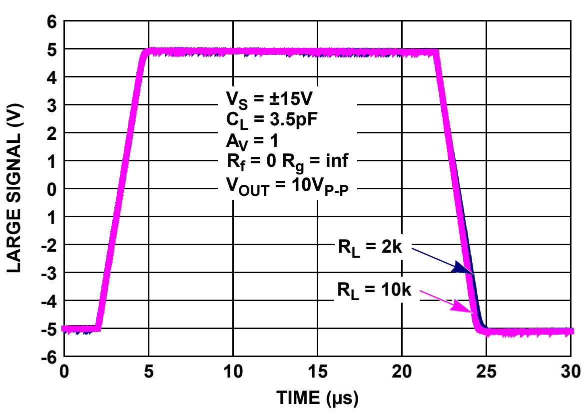


FIGURE 30. LARGE SIGNAL 10V STEP RESPONSE, V_S = ±15V

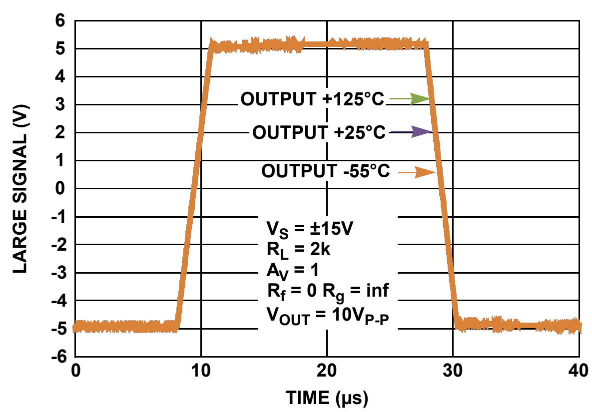


FIGURE 31. LARGE SIGNAL 10V STEP RESPONSE, V_S = ±15V vs TEMPERATURE

Typical Performance Curves

V_S = ±15V, V_{CM} = 0V, R_L = Open, T_A = +25°C, unless otherwise specified. **(Continued)**

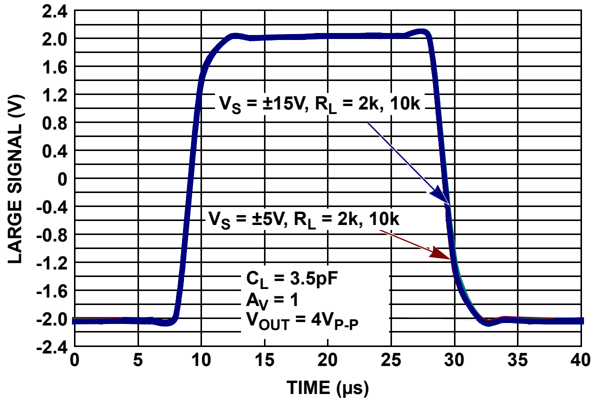


FIGURE 32. LARGE SIGNAL TRANSIENT RESPONSE vs R_L, V_S = ±5V, ±15V

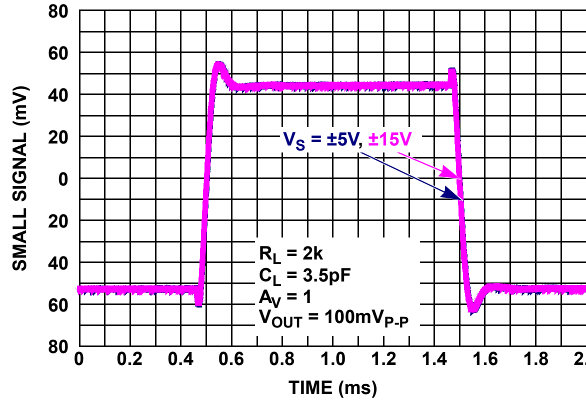


FIGURE 33. SMALL SIGNAL TRANSIENT RESPONSE, V_S = ±5V, ±15V

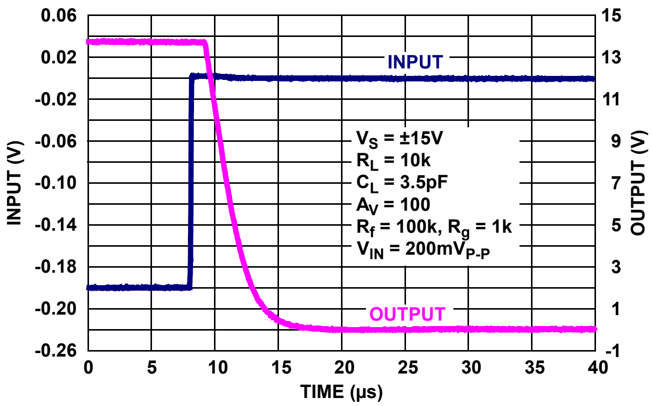


FIGURE 34. POSITIVE OUTPUT OVERLOAD RESPONSE TIME, V_S = ±15V

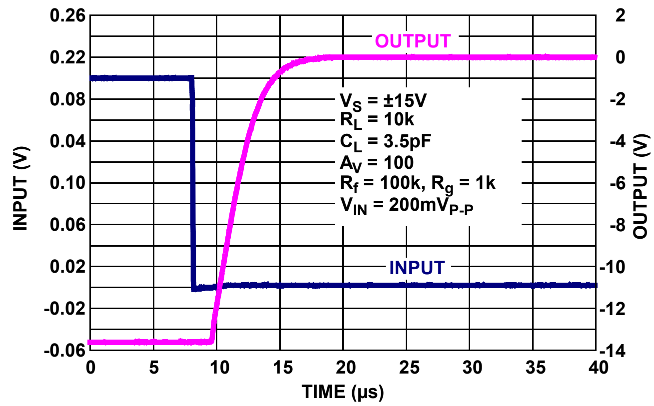


FIGURE 35. NEGATIVE OUTPUT OVERLOAD RESPONSE TIME, V_S = ±15V

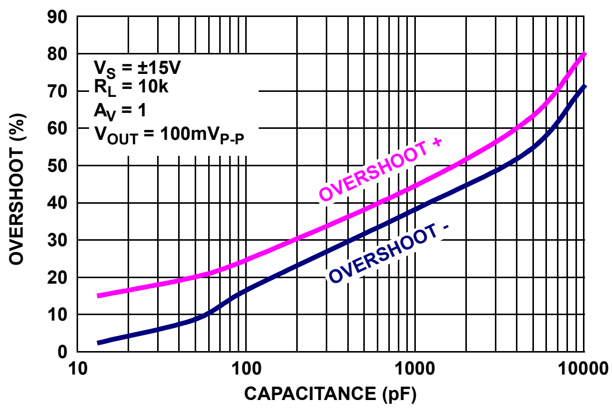


FIGURE 36. % OVERSHOOT vs LOAD CAPACITANCE, V_S = ±15V

Applications Information

Functional Description

The ISL70227SEH is a dual, low noise 10MHz BW precision op amp fabricated in a new precision 40V complementary bipolar DI process. A super-beta NPN input stage with input bias current cancellation provides low input bias current (1nA typical), low input offset voltage (10µV typ), low input noise voltage (3nV/√Hz), and low 1/f noise corner frequency (5Hz). These amplifiers also feature high open loop gain (1500V/mV) for excellent CMRR (120dB) and THD+N performance (0.0002% @ $3.5V_{RMS}$, 1kHz into 2kΩ). A complimentary bipolar output stage enables high capacitive load drive without external compensation.

Operating Voltage Range

The devices are designed to operate over the 4.5V (±2.25V) to 36V (±18V) range and are fully characterized at 30V (±15V). Parameter variation with operating voltage is shown in the "Typical Performance Curves" beginning on page 9.

Input ESD Diode Protection

The input terminals (IN+ and IN-) have internal ESD protection diodes to the positive and negative supply rails, and an additional anti-parallel diode pair across the inputs (see Figures 37 and 38).

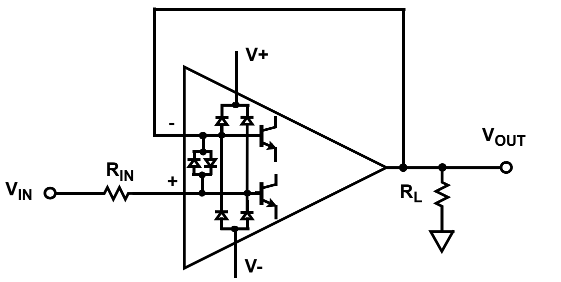


FIGURE 37. INPUT ESD DIODE CURRENT LIMITING - UNITY GAIN

For unity gain applications (see Figure 37) where the output is connected directly to the non-inverting input a current limiting resistor (R_{IN}) will be needed under the following conditions to protect the anti-parallel differential input protection diodes.

- The amplifier input is supplied from a low impedance source.
- The input voltage rate-of-rise (dV/dt) exceeds the maximum slew rate of the amplifier (±3.6V/µs).

If the output lags far enough behind the input, the anti-parallel input diodes can conduct. For example, if an input pulse ramps from 0V to +10V in 1µs, then the output of the ISL70227SEH will reach only +3.6V (slew rate = 3.6V/µs) while the input is at 10V, The input differential voltage of 6.4V will force input ESD diodes to conduct, dumping the input current directly into the output stage and the load. The resulting current flow can cause permanent damage to the ESD diodes. The ESD diodes are rated to 20mA, and in the previous example, setting R_{IN} to 1k resistor (see Figure 37) would limit the current to <6.4mA, and provide additional protection up to ±20V at the input.

In applications where one or both amplifier input terminals are at risk of exposure to high voltage, current limiting resistors may be needed at each input terminal (see Figure 38 $R_{IN}+$, $R_{IN}-$) to limit current through the power supply ESD diodes to 20mA.

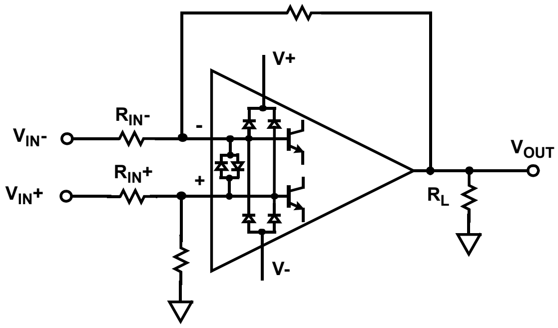


FIGURE 38. INPUT ESD DIODE CURRENT LIMITING - DIFFERENTIAL INPUT

Output Current Limiting

The output current is internally limited to approximately ±45mA at +25°C and can withstand a short circuit to either rail as long as the power dissipation limits are not exceeded. This applies to only one amplifier at a time. Continuous operation under these conditions may degrade long term reliability.

Output Phase Reversal

Output phase reversal is a change of polarity in the amplifier transfer function when the input voltage exceeds the supply voltage. The ISL70227SEH are immune to output phase reversal, even when the input voltage is 1V beyond the supplies.

Power Dissipation

It is possible to exceed the +150°C maximum junction temperatures under certain load and power supply conditions. It is therefore important to calculate the maximum junction temperature (T_{JMAX}) for all applications to determine if power supply voltages, load conditions, or package type need to be modified to remain in the safe operating area. These parameters are related using Equation 1:

$$T_{JMAX} = T_{MAX} + \theta_{JA} x PD_{MAXTOTAL} \quad \text{(EQ. 1)}$$

where:

- $P_{DMAXTOTAL}$ is the sum of the maximum power dissipation of each amplifier in the package (PD_{MAX})
- PD_{MAX} for each amplifier can be calculated using Equation 2:

$$PD_{MAX} = V_S \times I_{qMAX} + (V_S - V_{OUTMAX}) \times \frac{V_{OUTMAX}}{R_L} \quad \text{(EQ. 2)}$$

where:

- T_{MAX} = Maximum ambient temperature
- θ_{JA} = Thermal resistance of the package
- PD_{MAX} = Maximum power dissipation of one amplifier
- V_S = Total supply voltage
- I_{qMAX} = Maximum quiescent supply current of one amplifier
- V_{OUTMAX} = Maximum output voltage swing of the application
- R_L = Load resistance

Package Characteristics

Weight of Packaged Device

0. 4029 grams (Typical)

Lid Characteristics

Finish: Gold
Case Isolation to Any Lead: 20 x 10^9 Ω (min)

Die Characteristics

Die Dimensions

1565µm x 2125µm (62mils x 84mils)
Thickness: 355µm ± 25µm (14 mils ± 1 mil)

Interface Materials

GLASSIVATION

Type: Nitrox
Thickness: 15kÅ

TOP METALLIZATION

Type: AlCu (99.5%/0.5%)
Thickness: 30kÅ

BACKSIDE FINISH

Silicon

PROCESS

Dielectrically Isolated Complementary Bipolar - PR40

ASSEMBLY RELATED INFORMATION

SUBSTRATE POTENTIAL

Floating

ADDITIONAL INFORMATION

WORST CASE CURRENT DENSITY

< 2 x 10^5 A/cm^2

Metallization Mask Layout

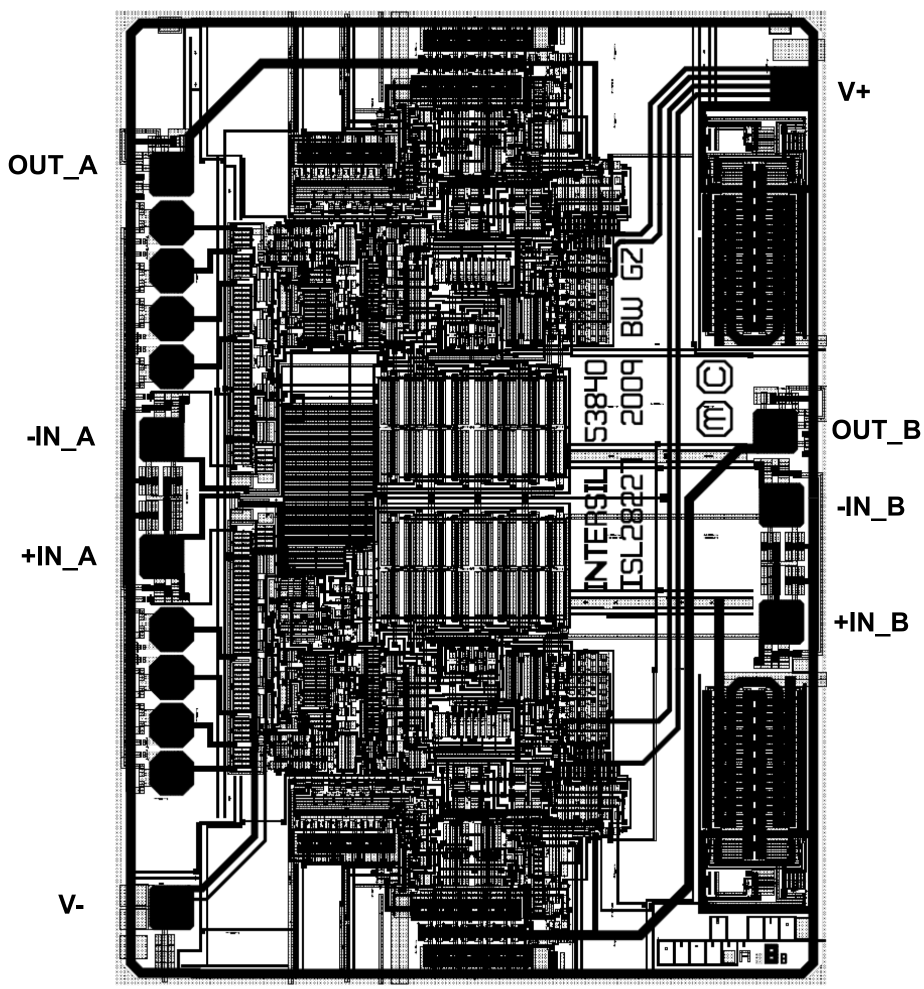


TABLE 1. DIE LAYOUT X-Y COORDINATES

PAD NAME	PAD NUMBER	X (µm)	Y (µm)	dX (µm)	dY (µm)	BOND WIRES PER PAD
OUT_A	11	0	1530	70	70	1
-IN_A	13	-20.5	976	70	70	1
+IN_A	14	-20.5	732	70	70	1
V-	9	0	0	70	70	1
+IN_B	16	1272.5	595.5	70	70	1
-IN_B	15	1272.5	839.5	70	70	1
OUT_B	12	1259.5	993.5	70	70	1
V+	10	1295.5	1708	70	70	1

NOTE:

6. Origin of coordinates is the centroid of pad 9.

Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to web to make sure you have the latest Rev.

DATE	REVISION	CHANGE
August 24, 2012	FN7958.1	Initial release.

Products

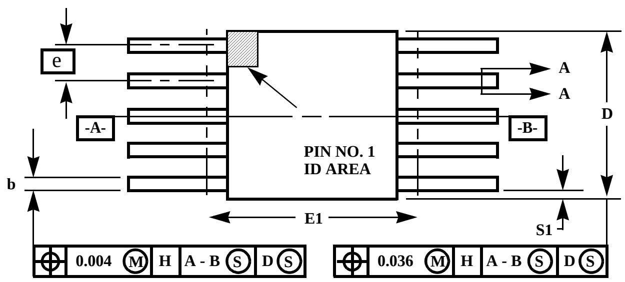
Intersil Corporation is a leader in the design and manufacture of high-performance analog semiconductors. The Company's products address some of the industry's fastest growing markets, such as, flat panel displays, cell phones, handheld products, and notebooks. Intersil's product families address power management and analog signal processing functions. Go to www.intersil.com/products for a complete list of Intersil product families.

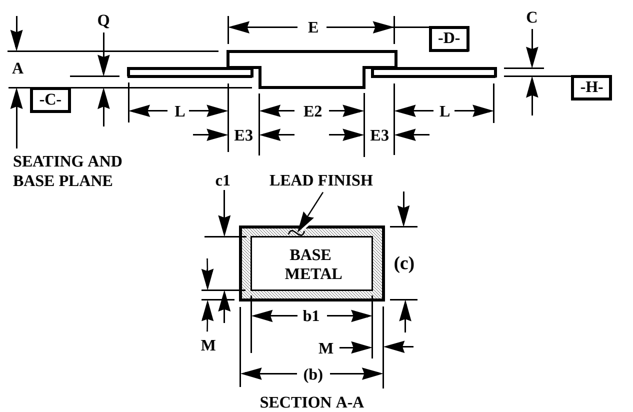
For a complete listing of Applications, Related Documentation and Related Parts, please see the respective device information page on intersil.com: ISL70227SEH

To report errors or suggestions for this datasheet, please go to www.intersil.com/askourstaff

FITs are available from our website at: http://rel.intersil.com/reports/search.php

Ceramic Metal Seal Flatpack Packages (Flatpack)





K10.A **MIL-STD-1835 CDFP3-F10 (F-4A, CONFIGURATION B)**
10 LEAD CERAMIC METAL SEAL FLATPACK PACKAGE

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.045	0.115	1.14	2.92	-
b	0.015	0.022	0.38	0.56	-
b1	0.015	0.019	0.38	0.48	-
c	0.004	0.009	0.10	0.23	-
c1	0.004	0.006	0.10	0.15	-
D	-	0.290	-	7.37	3
E	0.240	0.260	6.10	6.60	-
E1	-	0.280	-	7.11	3
E2	0.125	-	3.18	-	-
E3	0.030	-	0.76	-	7
e	0.050 BSC		1.27 BSC		-
k	0.008	0.015	0.20	0.38	2
L	0.250	0.370	6.35	9.40	-
Q	0.026	0.045	0.66	1.14	8
S1	0.005	-	0.13	-	6
M	-	0.0015	-	0.04	-
N	10		10		-

Rev. 0 3/07

NOTES:

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark. Alternately, a tab (dimension k) may be used to identify pin one.
2. If a pin one identification mark is used in addition to a tab, the limits of dimension k do not apply.
3. This dimension allows for off-center lid, meniscus, and glass overrun.
4. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
5. N is the maximum number of terminal positions.
6. Measure dimension S1 at all four corners.
7. For bottom-brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
8. Dimension Q shall be measured at the point of exit (beyond the meniscus) of the lead from the body. Dimension Q minimum shall be reduced by 0.0015 inch (0.038mm) maximum when solder dip lead finish is applied.
9. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
10. Controlling dimension: INCH.